
Session Title:	34. Oxide TFT Device Structure
Date:	Aug. 25, 2016 (Thursday)
Time:	08:30~09:45
Room	Room B (Halla B)
Session Chairs	Prof. Yukiharu Uraoka (NAIST, Japan) Prof. Saeroonter Oh (Hanyang Univ., Korea)

B34-1

08:30~08:55

[Invited] Achieving High Performance Metal Oxide Thin Film Transistors Through Structural and Post Treatment Engineering

Hyun Jae Kim (Yonsei Univ., Korea)

B34-2

08:55~09:20

[Invited] High Mobility Thin-Film Transistors Based on Solution Processed Low Dimensional Metal Oxides

Hendrik Faber, Yen-Hung Lin, Satyajit Das, Ivan Isakov, Nikolaos Chastas, and Thomas Anthopoulos (Imperial College London, U.K.)

B34-3

09:20~09:45

[Invited] Enhancement of Metal Oxide TFT Performance by Engineering of Channel/Insulator

Shi-Jin Ding (Fudan Univ., China)